NSN 5961-01-256-8881

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View Online at https://aerobasegroup.com/nsn/5961-01-256-8881 **Inclosure Material:** Metal **Overall Length:** 1.252 inches **Overall Height:** 0.340 inches **Overall Width:** 0.700 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 160.0 collector to base voltage/static/emitter open and 140.0 collector to emitter voltage/static/base open and 7.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 3.00 amperes source cutoff current and 2.00 amperes source cutoff current **Power Rating Per Characteristic:** 5.8 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Item must comply with requirements of defense electronics supply center production standard no. L03745; for navy nuclear propulsion plant products only; junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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